

# **UTC2SB776 PNP EPITAXIAL SILICON TRANSISTOR**

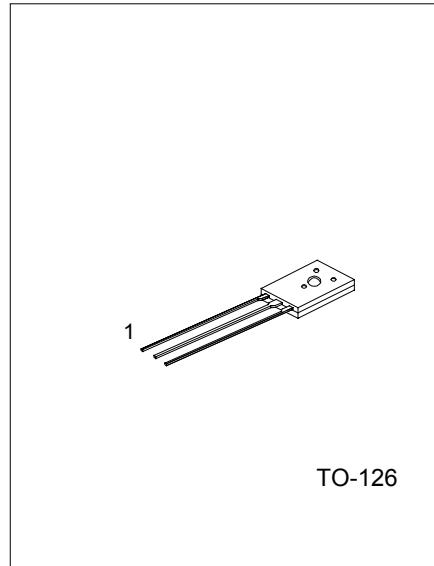
**MEDIUM POWER LOW VOLTAGE  
TRANSISTOR**

## **DESCRIPTION**

The UTC 2SB776 is a medium power low voltage transistor, designed for audio power amplifier, DC-DC converter and voltage regulator.

## **FEATURES**

- \*High current output up to 3A
- \*Low saturation voltage
- \*Complement to 2SD886



**TO-126**

1:EMITTER 2:COLLECTOR 3:BASE

## **ABSOLUTE MAXIMUM RATINGS ( Ta=25°C ,unless otherwise specified )**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>C EO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Dissipation (Tc=25°C)	P <sub>c</sub>	10	W
Collector Dissipation (Ta=25°C)	P <sub>c</sub>	1	W
Collector Current (DC)	I <sub>c</sub>	-3	A
Collector Current (PULSE)	I <sub>c</sub>	-7	A
Base Current	I <sub>B</sub>	-0.6	A
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>TG</sub>	-55 ~ +150	°C

## **ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-1000	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-3V, I <sub>c</sub> =0			-1000	nA
DC Current Gain(note 1)	h <sub>FE1</sub> h <sub>FE2</sub>	V <sub>CE</sub> =-2V, I <sub>c</sub> =-20mA V <sub>CE</sub> =-2V, I <sub>c</sub> =-1A	100 100	200 150	400	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =-2A, I <sub>B</sub> =-0.2A		-0.3	-0.5	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> =-2A, I <sub>B</sub> =-0.2A		-1.0	-2.0	V
Current Gain Bandwidth Product	f <sub>r</sub>	V <sub>CE</sub> =-5V, I <sub>c</sub> =-0.1A		80		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		45		pF

Note 1:Pulse test: PW<300μs, Duty Cycle<2%

**UTC UNISONIC TECHNOLOGIES CO. LTD**

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QW-R204-003,A

# UTC2SB776 PNP EPITAXIAL SILICON TRANSISTOR

## CLASSIFICATION OF hFE2

RANK	Q	P	E
RANGE	100-200	160-320	200-400

## TYPICAL PERFORMANCE CHARACTERISTICS

Fig.1 Static characteristics

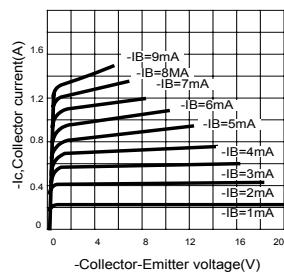


Fig.2 Derating curve of safe operating areas

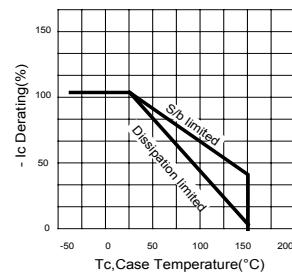


Fig.3 Power Derating

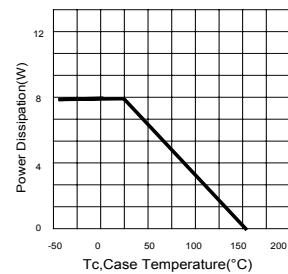


Fig.4 Collector Output capacitance

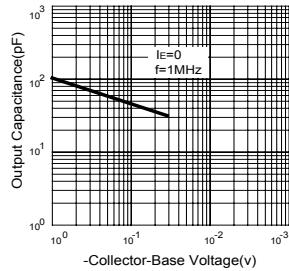


Fig.5 Current gain-bandwidth product

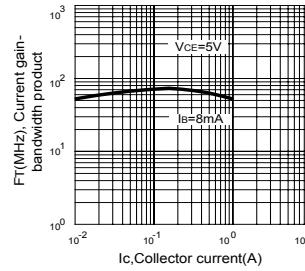


Fig.6 Safe operating area

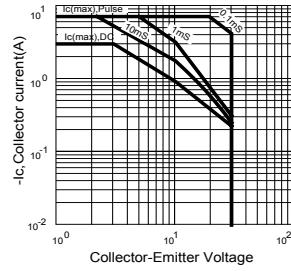


Fig.7 DC current gain

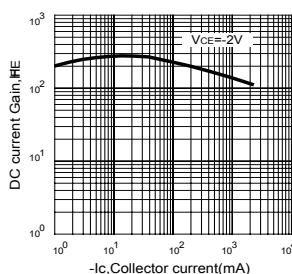
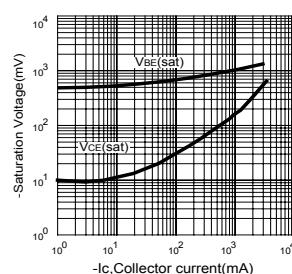


Fig.8 Saturation Voltage



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